What is claimed is:

1. A semiconductor chip comprising:

a first device formative layer with a thickness of at most 50μm provided over a thermal conductive substrate via a first adhesive layer;

a thermal conductive film formed on the first device formative layer; and

a second device formative layer with a thickness of at most 50μm formed over the thermal conductive film via a second adhesive layer.

2. The semiconductor chip according to Claim 1, wherein the first device formative layer and the second device formative layer have thicknesses of from 0.1 to 10μm.

3. The semiconductor chip according to Claim 1, wherein the thermal conductive substrate is formed of one of a ceramic material containing aluminum oxide, aluminum nitride, aluminum nitride oxide, or silicon nitride as its main components, and a graphite material containing carbon as its main components.

4. The semiconductor chip according to Claim 1, wherein the thermal conductive film comprises at least one selected from the group consisting of aluminum nitride, aluminum nitride oxide, boron phosphide, boron nitride, and diamond like carbon.

5. The semiconductor chip according to Claim 1, wherein at least one of the first device formative layer and the second device formative layer comprises at least one selected from the group consisting of a TFT, a CPU including TFTs, an MPU, a memory and a light-emitting apparatus.

6. An electric device having the semiconductor chip according to claim 1.

7. The electric device according to claim 6, wherein the electric device is one selected from the group consisting of a video camera, a digital camera, a head mounting display, a car navigation, a projector, a personal computer and a potable information terminal.

8. A semiconductor chip comprising:

a first device formative layer with a thickness of at most 50μm provided over a thermal conductive substrate via a first adhesive layer;

a thermal conductive film formed on the first device formative layer; and

a second device formative layer with a thickness of at most 50μm formed over the thermal conductive film via a second adhesive layer,

wherein each of the first device formative layer and the

second device formative layer is electrically connected to the thermal conductive substrate by a connection wire.

9. The semiconductor chip according to Claim 8, wherein the first device formative layer and the second device formative layer have thicknesses of from 0.1 to 10μm.

10. The semiconductor chip according to Claim 8, wherein the thermal conductive substrate is formed of one of a ceramic material containing aluminum oxide, aluminum nitride, aluminum nitride oxide, or silicon nitride as its main components, and a graphite material containing carbon as its main components.

11. The semiconductor chip according to Claim 8, wherein the thermal conductive film comprises at least one selected from the group consisting of aluminum nitride, aluminum nitride oxide, boron phosphide, boron nitride, and diamond like carbon.

12. The semiconductor chip according to Claim 8, wherein at least one of the first device formative layer and the second device formative layer comprises at least one selected from the group consisting of a TFT, a CPU including TFTs, an MPU, a memory and a light-emitting apparatus.

13. An electric device having the semiconductor chip

according to claim 8.

14. The electric device according to claim 13, wherein the electric device is one selected from the group consisting of a video camera, a digital camera, a head mounting display, a car navigation, a projector, a personal computer and a potable information terminal.

15. A semiconductor chip comprising:

a first device formative layer with a thickness of at most 50μm provided over a thermal conductive substrate via a first adhesive layer;

a thermal conductive film formed on the first device formative layer; and

a second device formative layer with a thickness of at most 50μm formed over the thermal conductive film via a second adhesive layer,

wherein a first semiconductor device included in the first device formative layer and a second semiconductor device included in the second device formative layer are electrically connected via the second adhesive layer by a first wiring included in the first device formative layer and an auxiliary wiring connected electrically to a second wiring included in the second formative layer.

16. The semiconductor chip according to Claim 15, wherein the

first device formative layer and the second device formative layer have thicknesses of from 0.1 to 10μm.

17. The semiconductor chip according to Claim 15, wherein the second adhesive layer contains an anisotropic conductive material.

18. The semiconductor chip according to Claim 15, wherein the thermal conductive substrate is formed of one of a ceramic material containing aluminum oxide, aluminum nitride, aluminum nitride oxide, or silicon nitride as its main components, and a graphite material containing carbon as its main components.

19. The semiconductor chip according to Claim 15, wherein the thermal conductive film comprises at least one selected from the group consisting of aluminum nitride, aluminum nitride oxide, boron phosphide, boron nitride, and diamond like carbon.

20. The semiconductor chip according to Claim 15, wherein at least one of the first device formative layer and the second device formative layer comprises at least one selected from the group consisting of a TFT, a CPU including TFTs, an MPU, a memory and a light-emitting apparatus.

21. An electric device having the semiconductor chip according to claim 15.

22. The electric device according to claim 21, wherein the electric device is one selected from the group consisting of a video camera, a digital camera, a head mounting display, a car navigation, a projector, a personal computer and a potable information terminal.

23. A method for manufacturing a semiconductor chip having a plurality of device formative layers with thicknesses of at most 50μm over a thermal conductive substrate, comprising the steps of:

fabricating a first device formative layer including a plurality of thin film transistors over a first substrate;

fabricating a soluble organic resin film over the first device formative layer;

fabricating a first adhesive layer in contact with the first soluble organic resin film;

bonding the second substrate to the first soluble organic resin film via the first adhesive layer, and sandwiching the first device formative layer and the first soluble organic resin film between the first substrate and the second substrate;

separating and removing the first substrate from the first device formative layer by a physical means;

fabricating a second adhesive layer in contact with the thermal conductive substrate;

bonding an exposed surface of the first device formative layer to the thermal conductive substrate via the second adhesive layer;

separating the first adhesive layer and the second substrate from the first device formative layer;

removing the first soluble organic resin film with solvent;

fabricating a thin film having thermal conductivity over an exposed surface;

fabricating a second device formative layer including a plurality of thin film transistors over a third substrate;

fabricating a second soluble organic resin film over the second device formative layer;

fabricating a third adhesive layer in contact with the second soluble organic resin film;

bonding the fourth substrate to the second soluble organic resin film via the third adhesive layer, and sandwiching the second device formative layer and the second soluble organic resin film between the third substrate and the fourth substrate;

separating and removing the third substrate from the second device formative layer by a physical means;

fabricating a fourth adhesive layer in contact with a thin film having thermal conductivity; and

an exposed surface of the second device formative layer over the thin film having thermal conductivity via the fourth adhesive layer.

24. The method for manufacturing the semiconductor chip according to Claim 23, wherein the third adhesive layer and the

fourth substrate are separated form the second device formative layer, and the second soluble organic resin film is remover with solvent.

25. The method for manufacturing the semiconductor chip according to Claim 23, wherein the thin film having thermal conductivity is formed of a film of aluminum nitride, aluminum nitride oxide, boron phosphide, boron nitride, or diamond like carbon, or a lamination film of these films, each of which is formed by sputtering.

26. The method for manufacturing the semiconductor chip according to Claim 23, either or both of the second adhesive layer and the fourth adhesive layer are formed by using an anisotropic adhesive, and the device formative layer is bonded via either or both of the second adhesive layer and the fourth adhesive layer by being irradiated with ultra waves.